

1006 Rec'd PCT/PTO 11 OCT 2005

PTO/SB/21 (09-04)

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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TRANSMITTAL FORM

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Total Number of Pages in This Submission

Application Number 10/525,283

Filing Date 02/16/2005

First Named Inventor James S. Im

Art Unit

Examiner Name

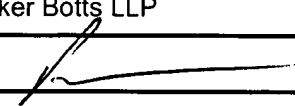
Attorney Docket Number A35185-PCT-USA (070050.2727)

ENCLOSURES (Check all that apply)

<input type="checkbox"/> Fee Transmittal Form	<input type="checkbox"/> Drawing(s)	<input type="checkbox"/> After Allowance Communication to TC
<input type="checkbox"/> Fee Attached	<input type="checkbox"/> Licensing-related Papers	<input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences
<input type="checkbox"/> Amendment/Reply	<input type="checkbox"/> Petition	<input type="checkbox"/> Appeal Communication to TC (Appeal Notice, Brief, Reply Brief)
<input type="checkbox"/> After Final	<input type="checkbox"/> Petition to Convert to a Provisional Application	<input type="checkbox"/> Proprietary Information
<input type="checkbox"/> Affidavits/declaration(s)	<input type="checkbox"/> Power of Attorney, Revocation	<input type="checkbox"/> Status Letter
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Remarks

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

Firm Name	Baker Botts LLP	Customer No.	21003
Signature			
Printed name	Paul A. Ragusa		
Date	10/07/2005	Reg. No.	38,587

CERTIFICATE OF TRANSMISSION/MAILING

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This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

11 OCT 2005

Applicants : Im et al. Customer No.: 21003
Serial No. : 10/525,283 Examiner : Not yet assigned
Filed : 02/16/2005 Group Art Unit: Not yet assigned
For : PROCESS AND SYSTEM FOR LASER CRYSTALLIZATION PROCESSING
OF FILM REGIONS ON A SUBSTRATE TO PROVIDE SUBSTANTIAL
UNIFORMITY WITHIN AREAS IN SUCH REGIONS AND EDGE AREAS
THEREOF, AND A STRUCTURE OF SUCH FILM REGIONS

INFORMATION DISCLOSURE STATEMENT

I hereby certify that this paper is being deposited with the
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October 7, 2005
Date of Deposit

Paul A. Ragusa
Attorney Name

38,587
Patent Reg. No.

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Signature

October 7, 2005
Date of Signature

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97(b), applicants bring to the attention of the
Examiner the documents listed on the attached Form PTO 1449 and respectfully request that the
listed documents be considered by the Examiner and made of record in the above-captioned
application. Copies of all U.S. Patents and Applications are not enclosed pursuant to the wavier

of 37 CFR 1.98 (a)(2)(i) for all applications filed after June 30, 2003. However, copies of all of the other documents listed on the Form PTO-1449 are enclosed herewith.

This submission does not represent that a search has been made or that no better art exists and does not constitute an admission that the listed documents are material or constitute "prior art." If the Examiner applies the documents as prior art against any claim in the application and applicants determine that the cited documents do not constitute "prior art" under United States law, applicants reserve the right to present to the Office the relevant facts and law regarding the appropriate status of the documents.

Applicants further reserve the right to take appropriate action to establish the patentability of the disclosed invention over the listed documents, should the documents be applied against the claims of the present application.

This Information Disclosure Statement is being before the mailing of a First Office Action. Therefore, applicants believe no fee is due. If any additional fee is due, or if any overpayment has been made, the Commissioner is authorized to charge any such fee or credit any overpayment, to our Deposit Account No. 02-4377.

Respectfully submitted,

BAKER BOTTS L.L.P.

By: 

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Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Atty. Docket No. A35185-PCT-USA (070050.2727)	Serial No. 10/525,283
	Applicant James S. Im	
	Filing Date 02/16/2005	Group TBD
	Examiner Not yet assigned	

U.S. PATENT DOCUMENTS

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
	1	3632205	01/04/1972	Marcy
	2	4234358	11/18/1980	Celler et al.
	3	4309225	01/05/1982	Fan et al.
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	14	4940505	07/1990	Schachameyer et al.
	15	4970546	11/1990	Suzuki et al.

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Examiner

Date Considered

* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	32	5529951	06/1996	Noguchi et al.
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	47	6120976	09/2000	Treadwell et al.
	48	6130009	10/2000	Smith et al.

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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
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Exam. Initial.	No.		Document No.	Issue/Publication Date	Applicant(s)
	130		6582827	06/24/2003	Im
	33		6830993	12/14/2004	Im et al.

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FOREIGN PATENT DOCUMENTS

Exam Initial	No.	Document No.	Publication Date	Country	Translation	
					Yes	No
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	91	1067593	10/01/2001	EP		
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	95	2338342	12/15/1999	GB		
	96	2283036	11/20/1990	JP		<u>No</u>
	97	6252048	09/09/1994	JP		<u>No</u>
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	100	11064883	03/05/1999	JP		<u>No</u>
	101	04033327		JP		<u>No</u>
	102	2001023920	01/26/2001	JP		
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Exam Initial	No.	Document No.	Publication Date	Country	Translation	
					Yes	No
	105	9931719	06/24/1999	WO		<u>No</u>
	106	0014784	03/16/2000	WO		
	107	0118854	03/15/2001	WO		
	108	0118855	03/15/2001	WO		
	109	0171786	09/27/2001	WO		
	110	02031869	04/18/2002	WO		
	111	02086954	05/30/2002	WO		
	112	9745827	12/04/1997	WO		
	113	0242847	05/30/2002	WO		
	114	03046965	06/05/2003	WO		
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	117	04017379	02/26/2004	WO		
	118	03084688	10/16/2003	WO		
	119	04017382	02/26/2004	WO		
	120	04017381	02/26/2004	WO		

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Exam Initial	No.		Document No.	Publication Date	Country	Translation	
						Yes	No
	121		04017380	02/26/2004	WO		
	122		04075263	08/19/2003	WO		

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Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)
✓	132	Im et al., "Controlled Super-Lateral Growth of Si Films for Microstructural Manipulation and Optimization", Phys. Stat. Sol. (a), vol. 166, p. 603 (1998).
✓	133	S.D. Brotherton et al., "Influence of Melt Depth in Laser Crystallized Poly-Si Thin Film Transistors," 82 J. Appl. Phys. 4086 (1997).
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✓	136	Sposili et al., "Sequential Lateral Solidification of Thin Silicon Films on SiO ₂ ", Appl. Phys. Lett., vol. 69 (19), p. 2864 (1996).*
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	143	K.H. Weiner et al., "Ultrashallow Junction Formation Using Projection Gas Immersion Laser Doping (PGILD)," A Verdant Technologies Technical Brief, Aug. 20, 1997.
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	145	McWilliams et al., "Wafer-Scale Laser Pantography: Fabrication of N-Metal-Oxide-Semiconductor Transistors and Small-Scale Integrated Circuits By Direct-Write Laser-Induced Pyrolytic Reactions," Applied Physics Letters, American Institute of Physics, New York, US, vol. 43, no. 10, Nov. 1983, pp. 946-948
	146	Mariucci et al., "Grain boundary location control by patterned metal film in excimer laser crystallized polysilicon," Proceedings of the Fifth International Conference on Polycrystalline Semiconductors, Schwabisch Gmund, Germany, Sept. 13-18, 1998, vol. 67-68, pp. 175-180
	147	Broadbent et al., "Excimer Laser Processing of Al-1%Cu/TiW Interconnect Layers," 1989 Proceedings, Sixth International IEEE VLSI Multilevel Interconnection Conference, Santa Clara, CA, June 12-13, 1989, pp. 336-345
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	152	Y. Miyata et al, "Low-Temperature Polycrystalline Silicon Thin-Film Transistors for Large-Area Liquid Crystal Display," 31 Japanese J. of Applied Physics Part 1--Regular Papers Short Notes & Review Papers, pp. 4559-62 (1992).
	153	Im <i>et al.</i> , "Phase Transformation Mechanisms Involved in Excimer Laser Crystallization of Amorphous Silicon Films," Appl. Phys. Lett., Vol. 63 (14), p. 1969 (1993).

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	Examiner Not yet assigned	

Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)
	154	Im <i>et al.</i> , "On the Super Lateral Growth Phenomenon Observed in Excimer Laser-Induced Crystallization of Thin Si Films," Appl. Phys. Lett., Vol. 64 (17), p. 2303 (1994).
	155	Brochure from MicroLas Lasersystem, GmbH, "UV Optics Systems for Excimer Laser Based Micromaching and Marking". 1999.
	156	Ishida et al., "Ultra-shallow boxlike profiles fabricated by pulsed ultraviolet-laser doping process", J. Vac. Sci. Technol. B 12(1), p. 399-403, 1994. (No month).
	157	Yoshimoto, et al., "Excimer-Laser-Produced and Two-Dimensionally Position-Controlled Giant Si Grains on Organic SOG Underlayer", p. 285-286, AM-LCD 2000. No month.
	158	Ozawa et al., "Two-Dimensionally Position-Controlled Exicem-Laser-Crystallization of Silicon Thin Films on Glassy Substrate", Jpn. J. Appl. Phys. vol. 38, Part 1, No. 10, p. 5700-5705, (1999). No month.
	159	I.W. Boyd, Laser Processing of Thin Films and Microstructures, Oxidation, Deposition, and Etching of Insulators (Springer--Verlag Berlin Heidelber 1987).*
	160	N. Yamamuchi and R. Reif, Journal of Applied Physics, "Polycrystalline silicon thin films processed with silicon ion implantation and subsequent solid-phase crystallization: Theory, experiments, and thin-film transistor applications" -- April 1, 1994 -- Volume 75, Issue 7, pp. 3235-3257
	161	T. Noguchi, "Appearance of Single-Crystalline Properties in Fine-Patterned Si Thin Film Transistors (TFTs) by Solid Phase Crystallization (SPC)," Jpn. J. Appl. Phys. Vol. 32 (1993) L1584-L1587
	162	Ishihara et al., "A Novel Double-Pulse Exicem-Laser Crystallization Method of Silicon Thin-Films," Japanese Journal of Applied Physics, Publication Office Japanese Journal of Applied Physics, Tokyo, Japan, vol. 34, no. 8A, August 1995, pp. 3976-3981
	163	Kim, H. J., "Excimer-Laser-Induced Crystallization of Amorophus Silicon Thin Films", Ph. D. Dissertation Abstract, Columbia University, 1996.*

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Examiner

Date Considered

* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.